

ABSTRACT OF THE DISCLOSURE

According to the invention, the thin film having the thickness controlled desirably can be easily formed using common semiconductor processes. Provided is a coating liquid for forming the porous film having an excellent dielectric property and mechanical property. Specifically, the coating liquid for forming a porous film comprises the condensation product obtained by condensation of one or more silicate compounds represented by the formula $(X_2O)_i(SiO_2)_j(H_2O)_k$ and one more organosilicate compounds represented by the formula $(X_2O)_a(RSiO_{1.5})_b(H_2O)_c$. Thus, the porous insulating film having sufficient mechanical strength and dielectric properties for use in the semiconductor manufacturing process can be manufactured.